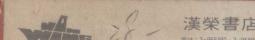
APPLIED ELECTRONICS

SECOND EDITION

Truman S Gray



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Applied Electronics

A FIRST COURSE IN ELECTRONICS, ELECTRON TUBES, AND ASSOCIATED CIRCUITS



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Foreword

The staff of the Department of Electrical Engineering at the Massachusetts Institute of Technology has for some years been engaged in an extensive program of revising as a unit its entire presentation of the basic technological principles of electrical engineering. This new edition of Applied Electronics covers a part of that presentation.

The decision to undertake so comprehensive a plan rather than to add here and patch there came from the belief that the Department's large staff, with its varied interests in teaching and related research, could effect a new synthesis of educational material in the field of electrical engineering and evolve a set of textbooks with a breadth of view not

easily approached by an author working individually.

Such a comprehensive revision, it was felt, should be free from the duplications, repetitions, and unbalances so often present in an unintegrated program. It should possess a unity and breadth arising from the organization of a subject as a whole. It should appeal to the student of ordinary preparation and also provide a depth and rigor challenging to the exceptional student and acceptable to the advanced scholar. should comprise a basic course adequate for all students of electrical engineering regardless of their ultimate specialty. Restricted to material which is of fundamental importance to all branches of electrical engineering, the course should naturally lead into any one branch.

This book and the reorganized program of teaching out of which it has grown are thus products of a major research project to improve educational methods. The rapid development of electronics brought about by the impetus of the recent wars has made desirable revision of the original book to include new and improved devices, techniques, and methods of presentation. During these developments it has become clear that revision of this treatment and extension of it to new areas such as are included in this book should become more and more the responsibility of individual authorities who could relate their work to the over-all structure.

KARL T. COMPTON

Preface

During the years since the first edition of this book was published, electronics has truly come of age. We now rely on it for our comfort, our convenience, and even our lives in diverse fields such as energy conversion, communication, and control. We look to it with justified expectancy for new useful developments of benefit to mankind. The importance of electronics in science and engineering and, correspondingly, in technological education, has thus become even more clearly established than ever before. To facilitate such education, this book aims to lay a foundation for effective engineering application of the basic phenomena of electronics.

The extent of the use of electronics in the different branches of electrical engineering—power, communications, measurement, control, and others—precludes a complete treatment of the subject in a single volume. Hence, this book is not exhaustive; details of application are expected to follow in courses designed for specialization by students in the different branches. This book is for a first basic course. Rigor of thought and analysis, rather than extensiveness of scope, is its intended feature.

New devices, new principles, and new methods of analysis have extended the possibilities for application of electronics. The basic pattern of the field, and hence of this book, remains, however, essentially unchanged from that of the original edition. On the premise that proper application of electronic apparatus requires a working knowledge of the physical phenomena involved in the apparatus, the first part of the book is a discussion of those phenomena. The second part is an explanation of the way the phenomena combine to govern the characteristics, ratings, and limitations of electronic devices, and the third is a consideration of applications common to the several branches of electrical engineering. Finally, the fourth part is a treatment of semiconductor devices, primarily the transistor, in a manner parallel to the previous treatment of vacuum tubes. This arrangement makes practicable use of the book as a textbook in a number of different ways. In its entirety, it is intended to be suitable for a two-semester course. Assigning the early chapters and certain of the later chapters as reference material for reading only, with resultant emphasis upon the chapters that treat the circuit applications of electron tubes and semiconductor devices, makes possible use of the book for a one-semester course. To provide for additional study by particularly apt or advanced students, more material than is usually covered in a first course is presented; and to aid independent study outside the classroom, graphical data on typical electron tubes and answers to representative problems stated at the ends of the chapters are included in appendices.

Most of the functional methods by which electronics is employed in engineering are included. To make the book adequate as a point of departure into independent study and analysis of specialized applications of electronics, emphasis is placed on care in reasoning, with the thought that ease of understanding is synonymous with clarity of conception. Attempt is made to point out all links in the chain of reasoning in order to avoid those gaps that are so easily spanned intuitively by experienced engineers, but are so disturbing to the careful but inexperienced student. In addition to exact logic, this effort involves not advanced mathematics, but rather scrupulous attention both to aids to clearness of thought and to apparently minor details that are elementary but essential. One important aid is precise definitions of symbols and interpretation of them in terms of physical quantities. Among the elementary details requiring attention are the algebraic signs associated with the distinction between actual and reference directions of quantities, and avoidance of the common error of mixing complex numbers and time functions in the same equation. The three categories of mathematical quantities-scalars, complex numbers, and vectors-are distinguished by distinctive type, in accordance with the ASA American Standard Letter Symbols for Electrical Quantities. Since some of the rules for mathematical manipulation of quantities in each of these categories differ from the rules for quantities in the other two categories, such a distinction is essential for clarity. Symbols for the various component currents and voltages in electron-tube circuits are consistent with the recently revised standard for those quantities, and rationalized meter-kilogramsecond units for physical quantities are used throughout the book, in accordance with almost universal present-day practice.

During preparation of this revision, it has been a pleasure to recall the contributions of colleagues who shared in supplying preliminary drafts of sections of the original edition. Many of them are now at other educational institutions or with industrial organizations; some, however, are still my close associates. The fact that many of the ideas and concepts in those early drafts continue to be regarded as fundamental and are hence retained in this revised book attests to the soundness of their judgment. I have been greatly aided by discussions with and suggestions from my present colleagues. In particular, I wish especially to thank Professor A. B. Van Rennes and Professor E. F. Buckley for their many

constructive suggestions throughout the book, and their able, generous, and untiring aid in reading all the manuscript and the proof. I am also indebted to Professor S. J. Mason and Professor R. E. Scott for their suggestions regarding circuit analysis, and to Professor R. B. Adler for his advice regarding the chapter on semiconductor devices. Dean F. G. Fassett, Jr., has been ever helpful with counsel on presentation and style, and Dean H. L. Hazen and Professor G. S. Brown have provided continual inspiration by their encouragement and support of this work. To all these individuals, and to my wife Isabel for her constant encouragement, assistance, and forbearance, I extend my thanks, with the hope that their helpfulness will be reflected in increased usefulness of the book to students.

TRUMAN S. GRAY

October 27, 1953

Table of Symbols

In this book a boldface roman-type or script letter is used to represent a space vector, and an ordinary italic or script letter to represent its magnitude, for example: $\mathbf{B}, \mathbf{E}, B, \mathbf{E}$. Similarly, a boldface italic letter is used to represent a complex number, and an italic letter its magnitude, for example: \mathbf{E}, \mathbf{E} . Ordinary italic or script letters are used to represent the ordinary real scalar quantities. For voltage, current, and charge, capital letters generally represent fixed quantities, and lower-case letters represent variable quantities. For transistors, however, an exception is made, as is explained in Art. 4, Ch. XIII. In general, each letter stands for a quantity of a particular kind, and subscripts are used to distinguish several quantities of the same kind from one another. For example, i is used for instantaneous current, and i_b specifies the instantaneous plate current in an electron tube.

The notation used in this book conforms to that standardized by the Institute of Radio Engineers¹ for use with electron tubes and their circuits. In order to make this conformity possible no distinction is made between e and v, or E and V. Any one is used to represent a voltage whether it be that of a source or not.

In the table that follows are listed the more important symbols used in this book. Many of the special symbols obtained through adding subscripts to the letters listed are omitted from this list, but are defined in the text where used. The standardized symbols used to designate voltage and current components encountered in electrontube circuits are omitted from the main list and appear instead in a table at the end of the list. This table is repeated in Art. 20, Ch. VIII.

Abbreviations used in this book are, in general, those approved by the American Standards Association.²

¹ Standards on Abbreviations, Graphical Symbols, Letter Symbols, and Mathematical Signs, 1948 (New York: The Institute of Radio Engineers, 1948), 1-9.

² American Standard Abbreviations for Scientific and Engineering Terms — ASA No. Z10.1 (New York: American Society of Mechanical Engineers, 1941).

TABLE OF SYMBOLS

ENGLISH LETTER SYMBOLS

	Symbo	l	Description Defin	ned o	r F	irst	Used
Complex	Scalar	Vector					Page
	A		Coefficient in Richardson's equation				77
	A		Heating current for a tungsten filament				88
	\overline{A}		Constant of integration				320
A	A		Voltage amplification of an amplifier				413
	\overline{A}		Amplitude of a wave				691
	A'		Heating current for a unit tungsten fila				88
	A_c		Amplitude of carrier wave				692
A_{fb}	A_{tb}		Voltage amplification of feedback ampli				5/73
A_{gg}	70		Loop transmission				575
99	A_m		Amplitude of modulating wave				692
	A_{oc}^m		Open-circuit voltage amplification .				804
A_{so}	00		Direct transmission				575
A_{t}			Complex no-load voltage amplification o	faf	eed	1-	
			back amplifier				589
	A(t)		Instantaneous amplitude of modulated	wa	ve		692
	a	a	Acceleration				8
	a		Coefficient in power series		~		440
	a		Transformer turns ratio				457
	a		A constant				735
	a		Amplitude of interfering signal				769
	a_1		Instantaneous current in anode 1 of po	lyp	has	se	
			rectifier				309
	B	В	Magnetic flux density				30
	B_{σ}		Input susceptance of vacuum tube .				422
	BW		Bandwidth				495
	b		Constant in Richardson's equation .				77
	b		Coefficient in power series				440
	C		Constant of integration				16
	C		Capacitance				317
	$C_{\mathfrak{e}}$		Capacitance of coupling capacitor .				509
	C_{q}		Capacitance of grid capacitor				642
	C_{g}'		Total interstage shunt capacitance in a	cas	cac	le	
			amplifier				515
	C_{gk}		Grid-to-cathode interelectrode capacita				420
	C_{gp}		Grid-to-plate interelectrode capacitance	€			420

	Symbo	bol Description Defined or F		First Used	
Complex	Scalar	Vector		Page	
	C_k	,	J I	398	
	C_{pk}		2 T	420	
	c		Speed of propagation of electromagnetic waves		
	-	_	in free space	100	
	D	D	Electric flux density	128	
	d		A distance	141	
	d		Diameter	$141 \\ 743$	
	d		Coefficient in power series	140	
177	$oldsymbol{E}$		Constant voltage	289	
E	,Ei		(See also table at end of this list for standard-	206	
			ized symbols for voltages encountered in		
			electron-tube circuits.)		
	E_{b}		Constant, or average, plate voltage of electron		
	D_b		tube	22	
	E_{bb}		Plate-supply voltage	118	
	E_{cc}		Grid-bias supply voltage	370	
	E_{dc}		Average value of rectifier load voltage	289	
	E_{d0}		Average value of rectified voltage	304	
	E_{d0}		Filament voltage of electron tube	172	
			Amplitude of alternating grid voltage	37'	
E	E_m		Extraneous or noise voltage	49	
E_n	E_n			57	
E_o	E_o		Output voltage	153	
-	E_s		Breakdown voltage of a gas	304	
E_s	E_s		Effective value of source voltage	282	
	E_{sm}		Maximum instantaneous value of source voltage	282	
	E_{0}		Voltage intercept for approximate plate characteristics	20	
	$\boldsymbol{E_0}$		Constant voltage drop in gas-type rectifier		
			when conducting	284	
	8	હ	when conducting		
	e		Instantaneous voltage	13	
	e_b		Tilbtailtaileous plate voltage of election	13	
	e_{e}		Instantaneous grid voltage of electron tube .	18	
	e_e		Instantaneous voltage across capacitor	719	
	e		Instantaneous grid-to-ground voltage	429	

	Symbo	l	Description	Defined or Firs	t Used
Complex	Scalur	Vector	,		Page
	e _{c1}		Instantaneous control-grid voltage tube		203
			tube		202
	e_{crit}		Critical grid voltage of a thyratron		366 304
	e_{d0}		Instantaneous rectified voltage .		
	e_{gna}		Sum component in grid-to-ground		505 505
	e_{gnd}		Difference component in grid-to-gro Instantaneous carrier voltage		738
	e_h		Instantaneous carrier voltage .		339
	e_i e_k		Instantaneous cathode-to-ground v		429
	e_k		Instantaneous modulating voltage		739
	e_o		Instantaneous output voltage .		431
	e_{o}		Local oscillator voltage		758
	e,		Instantaneous value of alterna	ting source	
	- 8		voltage	_	280
	e,		Input signal voltage		430
	e_t		Total radiation emissivity .		82
	e_0		Instantaneous control voltage of a		667
	e_1		Instantaneous source voltage for		
			polyphase rectifier		304
	\boldsymbol{F}	F	Force		4
	\mathbf{F}		Noise figure		816
	f		A function		58
	f		Frequency		111
	f		Fractional quantity		143
	f_0		Geometric mean frequency		519
	f_1		Lower half-power frequency .		515
	f_2		Upper half-power frequency		516
	G		Conductance	,	422
	G(f)		Frequency spectrum of a wave .		746
	G_{g}		Input conductance of vacuum tub	е	422
	$G(\omega)$)	Angular-frequency spectrum of a Mutual conductance, or control-	wave	702
	g_m		transconductance of vacuum tu		194
	h		Planck constant		194
	n I				80
	1		Constant current		80

	Symbo	l	Description Defined or First Use	ed
Complex	Scalar	Vector	Pa	_ ge
I	I		Effective value of alternating current 29 (See also table at end of this list for standard- ized symbols for currents encountered in	- 1 0
I,	I_{a} I_{b} I_{c} I_{dc} I_{dc} I_{f} I_{f} I_{L} I_{n}	1	electron-tube circuits.) Effective value of rectifier anode current	97 39 38 38 39 71 34 49 67 30 27 30
	i_b i_c i_c i_{c2}		Instantaneous plate current of electron tube . 11 Instantaneous grid current of electron tube . 19 Instantaneous capacitor current	7
	i_d i_i J J_s $J_n(\delta)$			8 7 7
	j K K		$\sqrt{-1}$	6 2 0
	$egin{array}{c} k \ k \ L \end{array}$,	Constant of proportionality	2 3 6
	l M	1	Length	

	Symbo	l	Description Defined or First Us	ed
Complex	Scalar	Vector	Pa	ige
	M		Atomic weight	63
	M			58
	M'			88
	m		Mass	4
	m		An integer)7
	m			98
	m_{e}		Rest mass of an electron	3
	N		Number	15
	N		Number of turns	95
	N(W)	Distribution function for kinetic energies .	38
	$N_x(V)$	V_{x}	Distribution function for x-associated kinetic	
				72
	n		Number per unit volume, area, length, or time	31
	n			7
	P		Average power	32
	P		Output power	10
	P_{ac}			16
	P_B	,	Power radiated by plate of electron tube 17	72
	P_{b}		Quiescent power input to plate of electron	
	-		tube	45
	P_{bb}		Power from plate power supply 44	15
	P_{bs}		Power input to plate of electron tube 6	16
	P_{cs}			37
	P_{dc}			90
	P_{g}		Power supplied by source of grid-signal voltage 6-	41
	P_h			10
	P_{in}		I I	90
	P_L		Power to load	15
	P_{m}		0 1	10
	P_{p}			90
	P_2		Rating of transformer secondary windings 3	10
	p^{-}		Pressure	12
	p			06
	\hat{Q}		Constant electric charge	6
	Q		Quiescent operating point	96
	Q		Ratio of reactance to resistance for an inductor 3	10
	Q_e		Magnitude of charge of electron	3

	Symbol		Description Defined or First U.	sed
Complex	Scalar	Vector	Pe	age
	Q_0		Figure of merit of a tuned circuit 5	49
	q			46
	R		The state of the s	46
	R		To 1	88
	R'			88
	$R_{\scriptscriptstyle b}$		Apparent resistance of plate circuit of Class C	
	7.		110	12
	R_{b}			94
	R_c		Core-loss resistance	36
	R_{eq}		Equivalent noise resistance	97
	R_{eq}		Equivalent shunt resistance in amplifier 5	14
	$R_{eq}{}'$		Equivalent series resistance in amplifier 5	14
	R_g		Resistance of grid resistor	00
	R_{in}			05
	R_k		Resistance of cathode resistor	98
	R_L		Resistance of load resistor	94
	Rout		Output resistance	05
	R_p		Effective primary-winding resistance to alter-	
				36
	R_{pp}		Plate-to-plate load resistance for push-pull	
				63
	R_{pri}		Primary-winding resistance 45	58
	R_S		Resistance of screen-grid voltage supply 42	26
	R_s		Internal resistance of source of grid signal 78	39
	R_s		Effective secondary-winding resistance to alter-	1
			nating current	36
	R_t		Tuned resistance of parallel-tuned circuit 55	50
	R_X		Resistance of filter inductor	10
	$R(\lambda)$		Photoelectric response function	4
	R_{0}		Resistance of vacuum-type rectifier when con-	
			ducting	
	R_1		Series grid resistor for thyratron 37	
	r			27
	r			33
	r_b		Base incremental resistance 80	
	r_c		Collector incremental resistance 80	
	r_{s}		Emitter incremental resistance 80	1

## Area of a surface		Symbol	l	Description Defined or First	Used
The final stream of the control of the cont	Complex	Scalar	Vector		Page
rm Mutual incremental resistance 801 rp Radius of plate of electron tube 50 rp Dynamic, or incremental, or variational, plate resistance of vacuum tube 194 r11 Incremental self-resistance 799 r12 Incremental transfer resistance 799 r21 Incremental transfer resistance 799 r22 Incremental self-resistance 799 8 Area of a surface 128 8p Area of plate of electron tube 132 T Absolute temperature 68 T Period of sinusoidal wave 447 t Time 8 Complex variable representing velocity in a plane 46 u A fraction 143 u Voltage across tungsten filament 88 V' Voltage across tungsten filament 88 V' Voltage across tungsten filament 88 V' Voltage across unit tungsten filament 88 V' Voltage across unit tungsten filament 88 <th< td=""><td></td><td>$r_{\rm h}$</td><td></td><td>Radius of cathode of electron tube</td><td>50</td></th<>		$r_{\rm h}$		Radius of cathode of electron tube	50
r _p Radius of plate of electron tube. 50 r _p Dynamic, or incremental, or variational, plate resistance of vacuum tube. 194 r ₁₁ Incremental self-resistance 799 r ₁₂ Incremental transfer resistance 799 r ₂₁ Incremental transfer resistance 799 s Area of a surface 128 s Area of plate of electron tube 132 T Absolute temperature 68 T Period of sinusoidal wave 447 t Time Complex variable representing velocity in a plane 46 u A fraction 143 u Variation in rectified voltage 355 V Voltage across tungsten filament 88 V' Voltage across unit tungsten filament 88 V' Voltage across unit tungsten filament 88 V' Voltage across unit tungsten filament 88 V' Instantaneous emitter-to-base voltage drop 793 V _o Emitter-bias supply voltage 793 V _o				Mutual incremental resistance	801
rp Dynamic, or incremental, or variational, plate resistance of vacuum tube. 194 r11 Incremental self-resistance 799 r12 Incremental transfer resistance 799 r21 Incremental transfer resistance 799 r22 Incremental self-resistance 799 s Area of a surface 128 s Area of plate of electron tube 132 T Absolute temperature 68 T Period of sinusoidal wave 447 t Time 8 Complex variable representing velocity in a plane 46 u A fraction 143 u Variation in rectified voltage 355 V Voltage across tungsten filament 88 V' Voltage across unit tungsten filament 88 V' Collector-bias supply voltage 793		***		Radius of plate of electron tube	50
resistance of vacuum tube. 194 \[r_{11} & Incremental self-resistance & 799 \] \[r_{12} & Incremental transfer resistance & 799 \] \[r_{21} & Incremental transfer resistance & 799 \] \[r_{21} & Incremental transfer resistance & 799 \] \[r_{22} & Incremental self-resistance & 799 \] \[s & Area of a surface & 128 \] \[s_p & Area of plate of electron tube & 132 \] \[T & Absolute temperature & 68 \] \[T & Period of sinusoidal wave & 447 \] \[t & Time & 8 \] \[Complex variable representing velocity in a plane & 46 \] \[u & A fraction & 143 \] \[u & Variation in rectified voltage & 355 \] \[V & Voltage across tungsten filament & 88 \] \[V' & Voltage across unit tungsten filament & 88 \] \[V' & Voltage across unit tungsten filament & 88 \] \[V' & Voltage across unit tungsten filament & 796 \] \[V_b & Base-bias supply voltage & 796 \] \[V_o & Collector-bias supply voltage & 793 \] \[V_o & Collector-bias supply voltage & 793 \] \[V_o & Emitter-bias supply voltage & 793 \] \[V_o & Emitter-bias supply voltage & 793 \] \[V_o & Emitter-bias supply voltage & 793 \] \[V_o & Emitter-bias supply voltage & 795 \] \[V_o & Emitter-bias supply voltage & 795 \] \[V_o & Emitter-bias supply voltage & 795 \] \[V_o & Emitter-bias supply voltage & 795 \] \[V_o & Emitter-bias supply voltage & 795 \] \[V_o & Emitter-bias supply voltage & 795 \] \[V_o & Emitter-bias supply voltage & 795 \] \[V_o & Emitter-bias supply voltage & 795 \] \[V_o & Emitter-bias supply voltage & 795 \] \[V_o & Emitter-bias supply voltage & 795 \] \[V_o & Emitter-bias supply voltage & 795 \] \[V_o & Emitter-bias supply voltage & 795 \] \[V_o & Emitter-bias supply voltage & 795 \] \[V_o & Emitter-bias supply voltage & 795 \] \[V_o & Emitter-bias supply voltage & 795 \] \[V_o & Emitter-bias supply voltage & 795 \] \[V_o & Emitter-bias supply voltage & 795 \] \[V_o & Emitter-bias supply voltage & 795 \] \[V_o & Emitter-bias supply voltage & 795 \] \[V_o & Emitter-bias supply voltage &				Dynamic, or incremental, or variational, plate	
r11 Incremental transfer resistance 799 r21 Incremental transfer resistance 799 r22 Incremental self-resistance 799 s Area of a surface 128 s Area of plate of electron tube 132 T Absolute temperature 68 T Period of sinusoidal wave 447 t Time 8 Complex variable representing velocity in a plane 46 u A fraction 143 u Variation in rectified voltage 355 V Voltage across tungsten filament 88 V' Voltage across tungsten filament 88 V' Voltage across unit tungsten filament 88 V' Voltage across unit tungsten filament 88 V' Voltage across unit tungsten filament 88 V' Instantaneous collector-to-base voltage drop 797 Vo Collector-bias supply voltage 793 Vo Emitter-bias supply voltage 789 Vo Emitte		y		resistance of vacuum tube	194
Tiz		r		Incremental self-resistance	799
r ₂₁ Incremental transfer resistance 799 r ₂₂ Incremental self-resistance 799 s Area of a surface 128 s, Area of plate of electron tube 132 T Absolute temperature 68 T Period of sinusoidal wave 447 t Time 8 Complex variable representing velocity in a plane 46 u A fraction 143 u Variation in rectified voltage 355 V Voltage across tungsten filament 88 V' Voltage across unit tungsten filament 89 V' Instantaneous collector-to-base voltage drop 797 V' Collector-bias supply voltage 793 V' Instantaneous emitter-to-base voltage drop 793 V' Instantaneous emitter-to-ground voltage drop 795					799
Total					799
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8p Area of plate of electron tube 132 T Absolute temperature 68 T Period of sinusoidal wave 447 t Time 8 Complex variable representing velocity in a plane 46 u A fraction 143 u Variation in rectified voltage 355 V Voltage across tungsten filament 88 V' Voltage across unit tungsten filament 88 V' Voltage across unit tungsten filament 88 V' Voltage across unit tungsten filament 88 V' Instantaneous base-to-emitter voltage drop 797 Vbb Base-bias supply voltage 796 Vc Instantaneous collector-to-base voltage drop 793 Vc Collector-bias supply voltage 793 Vc Emitter-bias supply voltage 789 Vc Instantaneous emitter-to-ground voltage drop 795 Vc Speed 4 Vne Collector noise voltage 814 vne Colle					128
## Absolute temperature					132
## Period of sinusoidal wave		-			68
$\begin{array}{cccccccccccccccccccccccccccccccccccc$		-			447
Complex variable representing velocity in a plane		_			8
plane	9.0				
u A fraction	86				46
u Variation in rectified voltage 355 V Voltage across tungsten filament 88 V' Voltage across unit tungsten filament 88 V_b Instantaneous base-to-emitter voltage drop 797 V_b Base-bias supply voltage 793 V_c Instantaneous collector-to-base voltage drop 793 V_c Collector-bias supply voltage 793 V_c Emitter-bias supply voltage 789 V_c Instantaneous emitter-to-ground voltage drop 795 V_c Instantaneous emitter-to-ground voltage drop 795 V_c Speed 4 V_c Collector noise voltage 814 V_{nc} Collector noise voltage 814 V_{nc} Emitter noise voltage 814 V_n Signal source voltage 789 W Power input to a tungsten filament 88 W Power input to a unit tungsten filament 88 W Potential-energy barrier at surface of a metal 72		24			143
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$\begin{array}{cccccccccccccccccccccccccccccccccccc$		V.		Voltage across unit tungsten filament	88
V_{bb} Base-bias supply voltage		V.		Instantaneous base-to-emitter voltage drop .	797
V_{ec} Instantaneous collector-to-base voltage drop . 793 V_{ec} Collector-bias supply voltage				Base-bias supply voltage	796
V_{ec}^{cc} Collector-bias supply voltage				Instantaneous collector-to-base voltage drop .	793
V. Instantaneous emitter-to-base voltage drop 793 V. Emitter-bias supply voltage 789 V. Instantaneous emitter-to-ground voltage drop 795 v Speed 4 v Velocity 32 v _{nc} Collector noise voltage 814 v _{ne} Emitter noise voltage 814 v _s Signal source voltage 789 W Energy 63 W Power input to a tungsten filament 88 W' Power input to a unit tungsten filament 88 W' Potential-energy barrier at surface of a metal 72					793
$\begin{array}{cccccccccccccccccccccccccccccccccccc$					793
Ven Instantaneous emitter-to-ground voltage drop 795 v Speed 4 v Velocity 32 v_ne Collector noise voltage 814 v_ne Emitter noise voltage 814 v_s Signal source voltage 789 W Energy 63 W Power input to a tungsten filament 88 W' Power input to a unit tungsten filament 88 W_a Potential-energy barrier at surface of a metal 72					789
$egin{array}{cccccccccccccccccccccccccccccccccccc$				Instantaneous emitter-to-ground voltage drop	795
$\begin{array}{cccccccccccccccccccccccccccccccccccc$					4
$egin{array}{cccccccccccccccccccccccccccccccccccc$		0	W	Velocity	32
v_{ne} Emitter noise voltage		91		Collector noise voltage	814
v _s Signal source voltage				Emitter noise voltage	814
W Energy					789
W Power input to a tungsten filament 88 W' Power input to a unit tungsten filament 88 Wa Potential-energy barrier at surface of a metal . 72					63
W' Power input to a unit tungsten filament 88 Wa Potential-energy barrier at surface of a metal . 72		***			88
W _a Potential-energy barrier at surface of a metal. 72				Power input to a unit tungsten filament	88
				Potential-energy barrier at surface of a metal.	72
		W_{i}^{a}		Energy level at top of Fermi band	68

_	Symbol	Description Defined or First	Used
Complex	Scalar		Page
	W_x	x-associated kinetic energy	71
	X	Reactance	325
	X_{c}	Reactance of capacitor	325
	X_L	Load reactance	409
	\boldsymbol{x}	A position co-ordinate	9
\boldsymbol{Y}_{g}	Y_{g}	Input admittance of a vacuum tube	422
	y	A position co-ordinate	9
	Z	Atomic number	63
Z	Z	Impedance	340
Z_{fb}	Z_{fb}	Driving-point impedance with feedback	586
Z_i	Z_i	Input impedance	433
Z_k	Z_k	Impedance in cathode circuit	417
Z_L	Z_L	Load impedance	409
Z_t	Z_t	Impedance of a tuned circuit	549
Z_t		Complex internal impedance of a feedback	
		amplifier	589
Z_{β}		Feedback transfer impedance	573
	z	A position co-ordinate	9
		GREEK LETTER SYMBOLS	
	α Alpha	Ratio of voltage drop in gas-type rectifier to	
	_	peak value of supply voltage	298
	α	A fraction	358
	α	Short-circuit current amplification	799
	α_e	Current ratio	801
	β Beta	Constant in three-halves-power equation for	
		cylindrical diode	133
β	β	Feedback voltage ratio	571
-	y Gamma	Ripple factor	291
	δ Delta	A ratio	45
	δ	Fractional deviation from resonant frequency.	550
	δ	A small error in experimental data	728
	δ	Modulation index	763
	ε Epsilon	Dielectric constant	129
	ε_v	Dielectric constant of free space	6
	€	Naperian base (2.71828)	46
	n Eta	Index of refraction	27

Symbol	Description Defined or Firs	t Used
Scalar		l'age
η	Efficiency	290
η_n	Plate efficiency of a vacuum tube	448
θ Theta	An angle	36
θ	Impedance angle	409
θ_A	Angle of complex voltage amplification	413
λ Lambda	Wavelength	5
. λ	Mean free path	141
μ Mu	Amplification factor of vacuum tube	189
ν Nu	Volume	128
ν	Number of collisions per centimeter	142
π Pi	Ratio of circumference to diameter of circle	
	(3.14159)	6
ρ Rho	Charge density	128
φ Phi	An angle	30
φ	Phase angle of current	410
φ	Voltage equivalent of work function	73
ϕ_c	Contact potential difference	75
$\phi(t)$	Instantaneous phase angle of modulated wave	691
ψ Psi	Phase angle of voltage	55
ω Omega	Angular frequency	55
ω_c	Angular frequency of carrier wave	692
ω_m	Angular frequency of modulating wave	692
$\omega(t)$	Instantaneous angular frequency of modulated	
	wave	693
ω_0	Resonant angular frequency	548
	OTHER SYMBOLS	
~	Approximately equal to	327
=	Defined as	193
>	Large compared with	341
«	Small compared with	341
Σ	Sum of	636
A	Magnitude of A	307
Δ	Increment of	29
	Dot product	10
×	Cross product	32
grad	Gradient of	8
Prese		-